General Purpose Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ic	-600	mAdc
Collector Current – Peak (Note 3)	I _{CM}	-1200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation – FR–5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation – Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Total Device Dissipation – Heat Spreader or equivalent, (Note 4) @T _A = 25°C	P _D	350	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

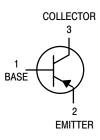
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.
- 3. Reference SOA curve.
- 4. Heat Spreader or equivalent = 450 mm², 2 oz.



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SOT-23 (TO-236AB) CASE 318 STYLE 6

MARKING DIAGRAM



2F = Device Code M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

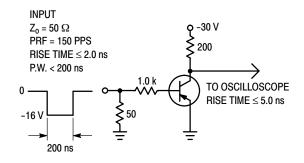
Device	Package	Shipping [†]
MMBT2907ALT1G	SOT-23	3000 / Tape &
SMMBT2907ALT1G	(Pb-Free)	Reel
MMBT2907ALT3G	SOT-23	10,000 / Tape &
SMMBT2907ALT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		·		-L	1
Collector-Emitter Breakdown Voltage (No $(I_C = -1.0 \text{ mAdc}, I_B = 0)$ $(I_C = -10 \text{ mAdc}, I_B = 0)$	te 5)	V _{(BR)CEO}	-60 -60	- -	Vdc
Collector – Base Breakdown Voltage (I _C :	V _{(BR)CBO}	-60	-	Vdc	
Emitter – Base Breakdown Voltage (I _E = -	-10 μAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = −30 Vdc,	$V_{EB(off)} = -0.5 \text{ Vdc}$	I _{CEX}	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	I _{CBO}	- -	-0.010 -10	μAdc	
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EI}	$B_{\text{Off}} = -0.5 \text{ Vdc}$	I _{BL}	-	-50	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -150 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -500 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}) \end{aligned} $	te 5)	h _{FE}	75 100 100 100 50	- - 300 -	-
Collector – Emitter Saturation Voltage (Not $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ (Not $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$,	V _{CE(sat)}		-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	5)	V _{BE(sat)}	- -	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	•
Current – Gain – Bandwidth Product (Not (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 10		f _T	200	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E :	= 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = −2.0 Vdc, I _C =	0, f = 1.0 MHz)	C _{ibo}	_	30	
SWITCHING CHARACTERISTICS					
Turn-On Time		t _{on}	ı	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _d	_	10	
Rise Time	,	t _r	_	40	no
Turn-Off Time		t _{off}	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t _s	_	80	
Fall Time	.61 – .62 – .0 (00)	t _f	-	30	

- 5. Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
- 6. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.





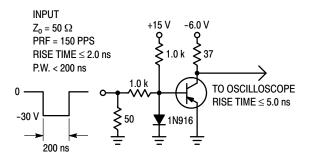


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

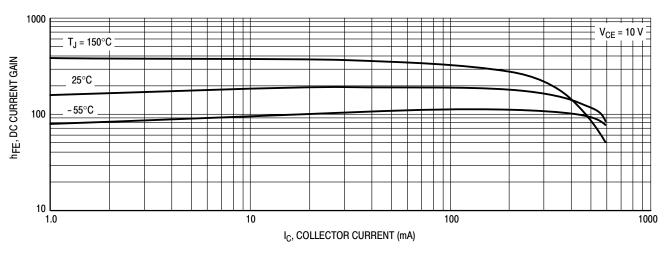


Figure 3. DC Current Gain

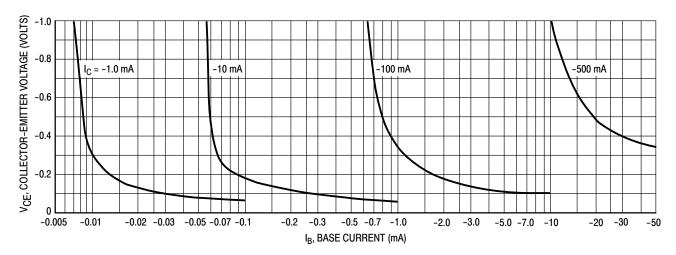


Figure 4. Collector Saturation Region

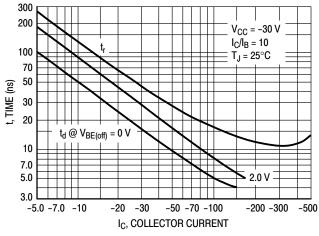


Figure 5. Turn-On Time

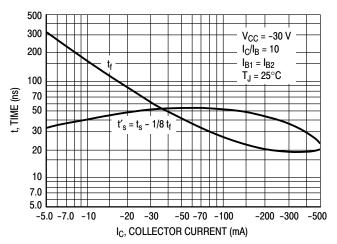
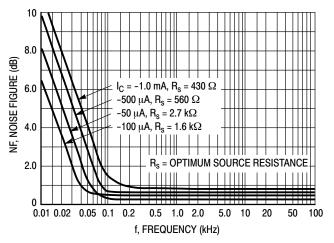


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

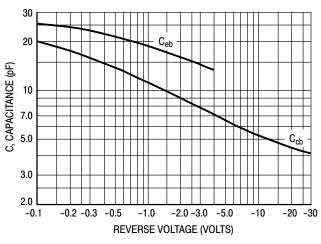
 V_{CE} = 10 Vdc, T_A = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0 $I_C = -50 \mu A$ -100 μA -500 μA 4.0 1.0 mA 2.0 100 200 2.0 k 50 k **5**0 1.0 k 5.0 k 10 k 20 k R_s, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



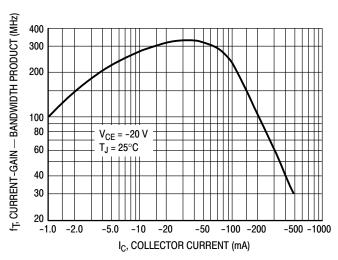
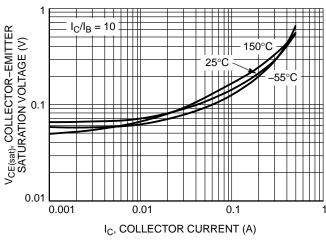


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



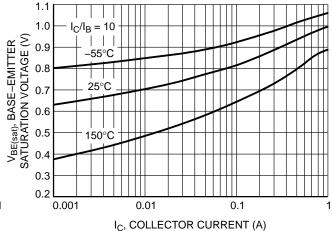
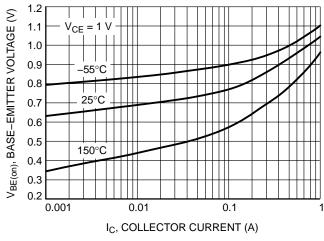


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Saturation Voltage vs.
Collector Current

TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C



+0.5

0

R₀VC for V_{CE(sat)}

-1.5

-2.0

R₀VB for V_{BE}

-2.5

-0.1 -0.2 -0.5 -1.0 -2.0 -5.0 -10 -20 -500

I_C, COLLECTOR CURRENT (mA)

Figure 13. Base Emitter Voltage vs. Collector Current

Figure 14. Temperature Coefficients

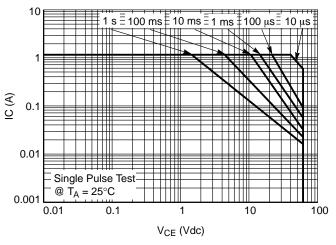
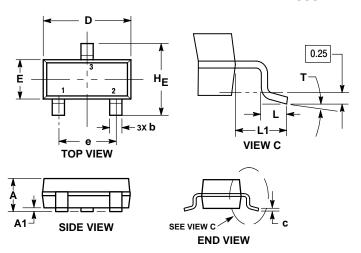


Figure 15. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
 BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

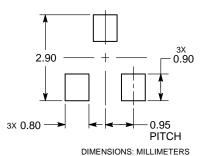
	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 6:

BASE PIN 1.

- 2. **EMITTER**
- COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT



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